

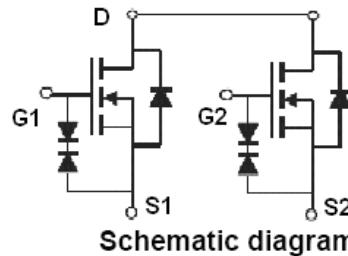
SED8830A **Dual N-Channel Enhancement Mode Field Effect Transistor**

Revision:A

Features

For a single mosfet

- $V_{DSS} = 20 \text{ V}$
- $R_{DS(\text{ON})} = 14.5 \text{ m}\Omega @ V_{GS}=4.5\text{V}$
- $R_{DS(\text{ON})} = 22 \text{ m}\Omega @ V_{GS}=2.5\text{V}$

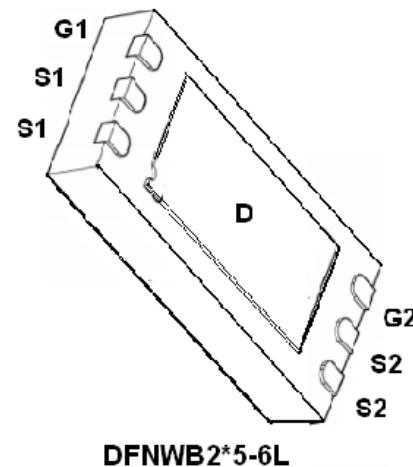


Applications

- Battery protection
- Load switch
- Power management

Construction

- Silicon epitaxial planer



Absolute Maximum Ratings

Paramet		Symbol	Rating	Units
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	± 12	V
Drain Current (Note 1)	Continuous	I_D	7	A
	Pulsed	I_{DM}	28	
Drain-Source Diode Forward Current		I_S	1.7	A
Maximum Power Dissipation		P_D	1.5	W
Operating Junction Temperature Range		T_J	-55 to 150	°C
Storage Temperature Range		T_{STG}		

SED8830A

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)						
Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
B_{VDS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{ V}$	20			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=16\text{ V}$, $V_{GS}=0\text{ V}$			1	μA
I_{GSS}	Gate-Body leakage	$V_{DS}=0\text{ V}$, $V_{GS}=\pm 10\text{ V}$			± 10	μA
ON CHARACTERISTICS						
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	0.5	0.8	1.3	V
$R_{DS(\text{ON})}$	Static Drain-Source On-Resistance	$V_{GS}=4.5\text{ V}$, $I_D=5\text{ A}$	-		14.5	$\text{m}\Omega$
		$V_{GS}=2.5\text{ V}$, $I_D=3\text{ A}$	-		22	
g_{FS}	Forward Transconductance	$V_{DS}=5\text{ V}$, $I_D=5\text{ A}$		1		S
DYNAMIC						
C_{iss}	Input Capacitance	$V_{GS}=0\text{ V}$, $V_{DS}=8\text{ V}$, $f=1.0\text{MHz}$		69		pF
C_{oss}	Output Capacitance			18		pF
C_{rss}	Reverse Transfer Capacitance			13		pF
SWITCHING						
Q_g	Total Gate Charge	$V_{GS}=4.0\text{ V}$, $V_{DS}=10\text{ V}$		11		nC
Q_{gs}	Gate Source Charge	$I_D=5\text{ A}$		1.8		
Q_{gd}	Gate Drain Charge			4.9		
$t_{d(on)}$	Turn-On Delay Time	$V_{GEN}=4.0\text{ V}$, $R_{GEN}=10\Omega$ $V_{DD}=10\text{ V}$, $I_D=1\text{ A}$		31		ns
$t_{d(off)}$	Turn-Off Delay Time			96		
$t_{d(r)}$	Turn-On Rise Time			62		
$t_{d(f)}$	Turn-Off Fall Time			40		
<p>Figure 1 shows the output characteristics of the SED8830A. The x-axis is V_{DS}, Drain-to-Source Voltage (V) from 0 to 3. The y-axis is I_D, Drain Current (A) from 0 to 15. Four curves are plotted for $V_{GS}=4\text{ V}$, 2.5 V, 2 V, and 1.5 V. As V_{GS} decreases, the drain current increases for a given V_{DS}.</p>						

Figure 1. Output Characteristics

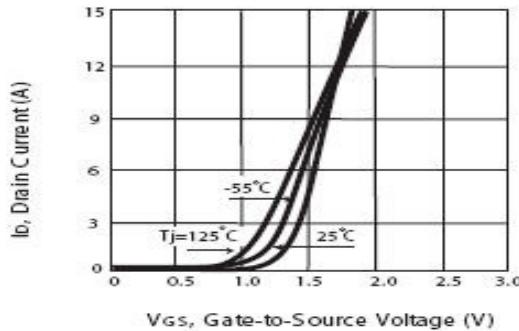


Figure 2. Transfer Characteristics

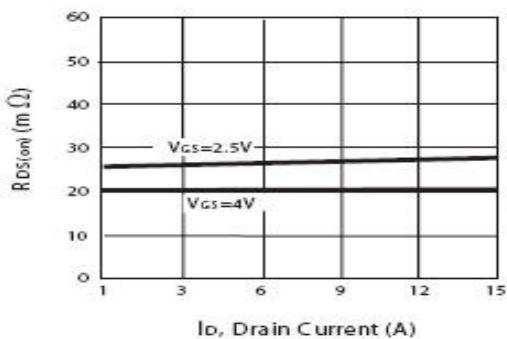


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

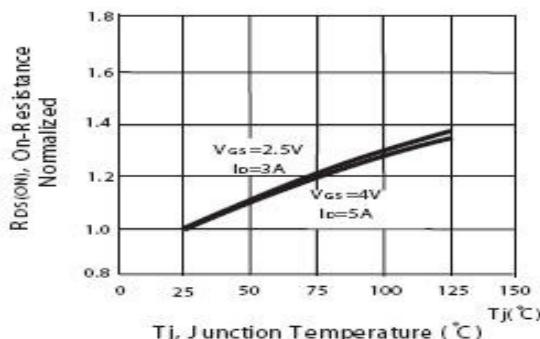


Figure 4. On-Resistance Variation with Drain Current and Temperature

SED8830A

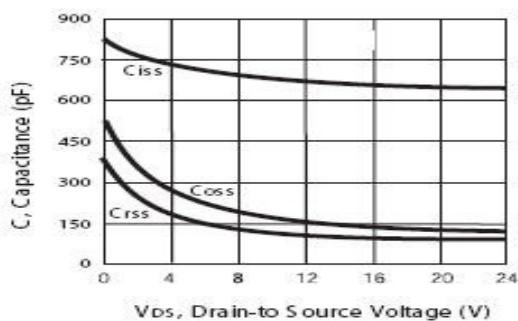


Figure 9. Capacitance

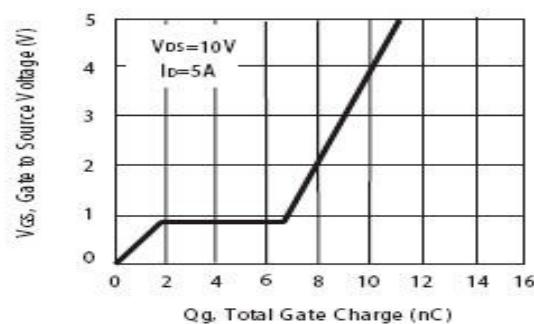


Figure 10. Gate Charge

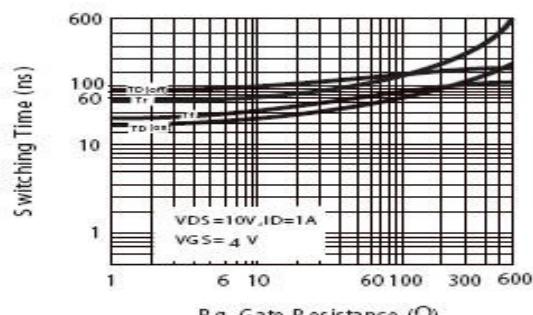


Figure 11. switching characteristics

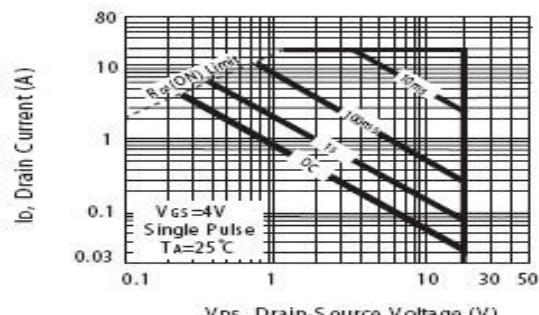


Figure 12. Maximum Safe Operating Area

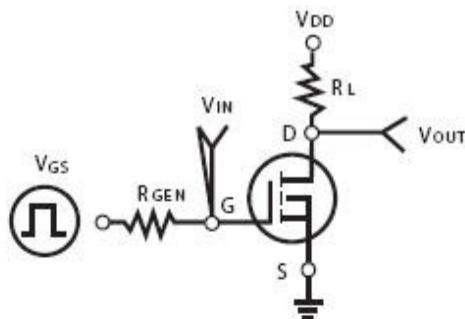


Figure 11. Switching Test Circuit

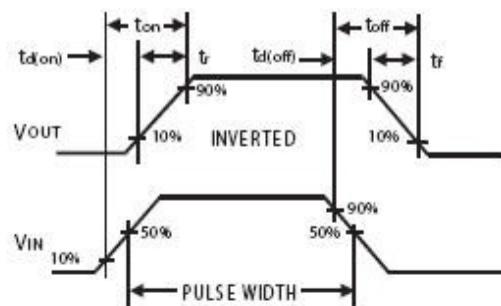
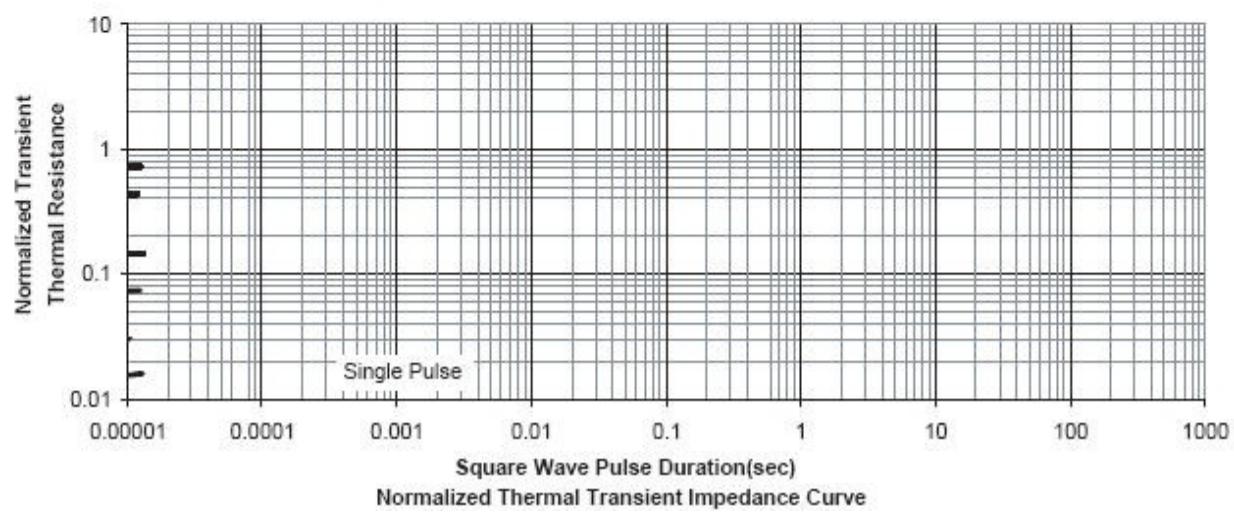
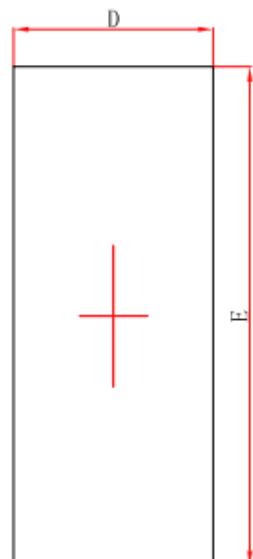


Figure 12. Switching Waveforms

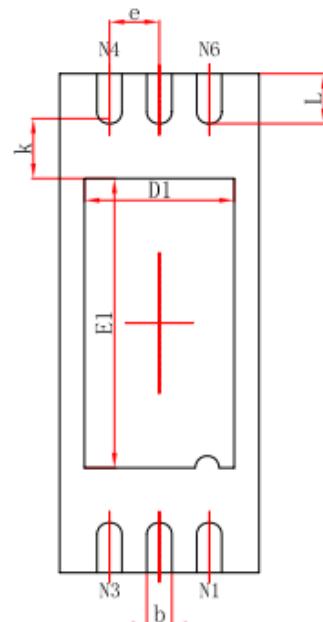


PACKAGE DIMENSION (Unit:mm)

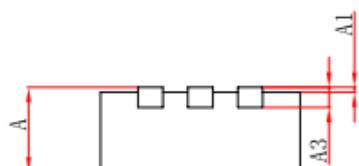
DFNWB2*5-6L



Top View



Bottom View



Side View

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700/0.800	0.800/0.900	0.028/0.031	0.031/0.035
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	1.924	2.076	0.076	0.082
E	4.924	5.076	0.194	0.200
D1	1.400	1.600	0.055	0.063
E1	2.800	3.000	0.110	0.118
k	0.200MIN.		0.008MIN.	
b	0.200	0.300	0.008	0.012
e	0.500TYP.		0.020TYP.	
L	0.374	0.526	0.015	0.021

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